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## EAST History

7/12/2005

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BRS	7105	finite adj state adj machine	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	0	S18 and (backgate adj voltages)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	0	S18 and (backgate adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	1	S18 and (back-gate adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	1	S18 and (back-gate adj voltages)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	871	S18 and transistors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	263	S18 and (circuit adj blocks)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	95	S24 and transistors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
IS&R	290	(326/46).CCLS.	US-PGPUB; USPAT; USOCR	12-Jul-05
BRS	17	S18 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	3416	(finite-state adj machine) or FSM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	8221	S18 or S28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	4	S29 and ((back-gate) or (back adj gate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	12-Jul-05
BRS	26	double-gate adj TFT	US-PGPUB; USPAT;	12-Jul-05
BRS	16	double-gate adj (thin adj film adj	US-PGPUB; USPAT;	12-Jul-05
BRS	2	double-gate adj (thin-film adj transistor)	US-PGPUB; USPAT;	12-Jul-05
BRS	0	S34 and ((back-gate) or (back adj gate))	US-PGPUB; USPAT;	12-Jul-05
BRS	16	S32 or S33	US-PGPUB; USPAT;	12-Jul-05